



SLPS292-JANUARY 2011

www.ti.com

P-Channel NexFET[™] Power MOSFET

Check for Samples: CSD25303W1015

FEATURES

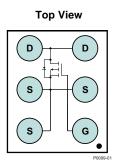
- Ultra Low Qg and Qgd
- Small Footprint
- Low Profile 0.62mm Height
- Pb Free
- RoHS Compliant
- Halogen Free
- CSP 1 × 1.5 mm Wafer Level Package

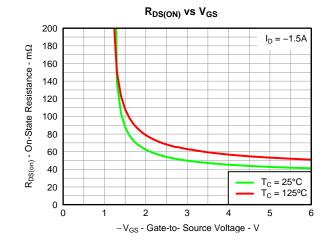
APPLICATIONS

- Battery Management
- Load Switch
- Battery Protection

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.





PRODUCT SUMMARY

T _A = 25°	C unless otherwise stated	TYPICAL VA	UNIT		
V _{DS}	Drain to Source Voltage -20				
Qg	Gate Charge Total (4.5V)	3.3	nC		
Q _{gd}	Gate Charge Gate to Drain	0.6	nC		
		$V_{GS} = -1.8V$	72	mΩ	
R _{DS(on)} Drain to Source On Resista		$V_{GS} = -2.5V$	= -2.5V 56		
		V _{GS} = -4.5V 46		mΩ	
V _{GS(th)}	Voltage Threshold	-0.65	V		

ORDERING INFORMATION

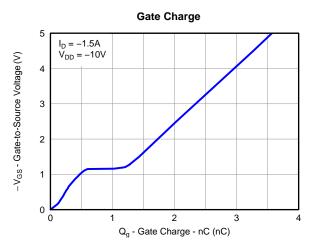
Device	Package	Media	Qty	Ship
CSD25303W1015	1 × 1.5 Wafer Level Package	7-inch reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT	
V _{DS}	Drain to Source Voltage	-20	V	
V_{GS}	Gate to Source Voltage	±8	V	
I _D	Continuous Drain Current, $T_C = 25^{\circ}C^{(1)}$	-3	Α	
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	-9	Α	
PD	Power Dissipation ⁽¹⁾	1.5	W	
T _{STG}	Storage Temperature Range	EE to 150	•0	
T _J ,	Operating Junction Temperature Range	-55 to 150 °C		

(1) Typical R_{θ JA} = 90°C/W on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.

(2) Pulse width ≤ 1 ms, duty cycle $\leq 2\%$



A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

SLPS292-JANUARY 2011



www.ti.com



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

· A – 20	°C unless otherwise stated) PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics	TEST CONDITIONS	IVITIN	1117	MAA	
	Drain to Source Voltage	<u> </u>	-20			V
BV _{DSS}	Ũ	$V_{GS} = 0V, I_D = -250\mu A$	-20		4	
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = -16V$			-1	μA
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 8V$			-100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.65	-1	V
		$V_{GS} = -1.8V, I_D = -1.5A$	72		92	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -1.5A$		56	71	mΩ
		$V_{GS} = -4.5V, I_D = -1.5A$		46	58	mΩ
g _{fs}	Transconductance	$V_{DS} = -10V, I_{D} = -1.5A$		9.6		S
Dynamic	Characteristics				·	
C _{ISS}	Input Capacitance			335	435	pF
C _{OSS}	Output Capacitance	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		149	191	pF
C _{RSS}	Reverse Transfer Capacitance			50	65	pF
R _g				0.6	1.2	Ω
Q _g	Gate Charge Total (-4.5V)			3.3	4.3	nC
Q _{qd}	Gate Charge Gate to Drain			0.6		nC
Q _{gs}	Gate Charge Gate to Source	$V_{\rm DS} = -10V, I_{\rm D} = -1.5A$		0.6		nC
Q _{g(th)}	Gate Charge at Vth			0.3		nC
Q _{OSS}	Output Charge	$V_{DS} = -11V, V_{GS} = 0V$		2.5		nC
t _{d(on)}	Turn On Delay Time			3.9		ns
t _r	Rise Time	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -1.5A		8.6		ns
t _{d(off)}	Turn Off Delay Time	$R_{G} = 4\Omega$		11.3		ns
t _f	Fall Time			7.8		ns
Diode C	haracteristics	1				
V _{SD}	Diode Forward Voltage	I _S = -1.5A, V _{GS} = 0V		-0.72	-1	V
Q _{rr}	Reverse Recovery Charge			3.6		nC
t _{rr}	Reverse Recovery Time	V_{dd} = -11V, I _F = -1.5A, di/dt = 200A/µs		11.3		ns

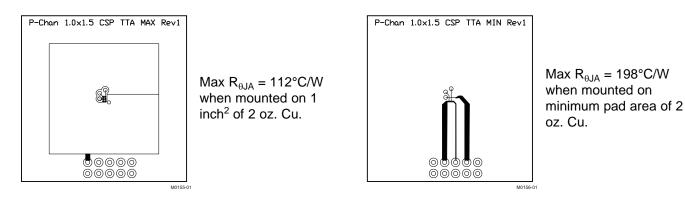
THERMAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$								
	PARAMETER	MIN	TYP	MAX	UNIT			
D	Thermal Resistance Junction to Ambient (Minimum Cu area)			198	°C/W			
R _{θJA}	Thermal Resistance Junction to Ambient (1 in ² Cu area)			112	°C/W			



www.ti.com





TYPICAL MOSFET CHARACTERISTICS

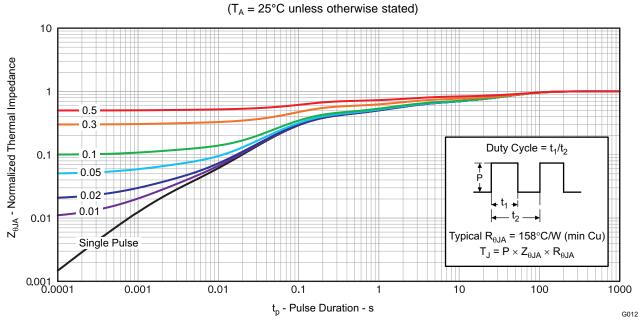
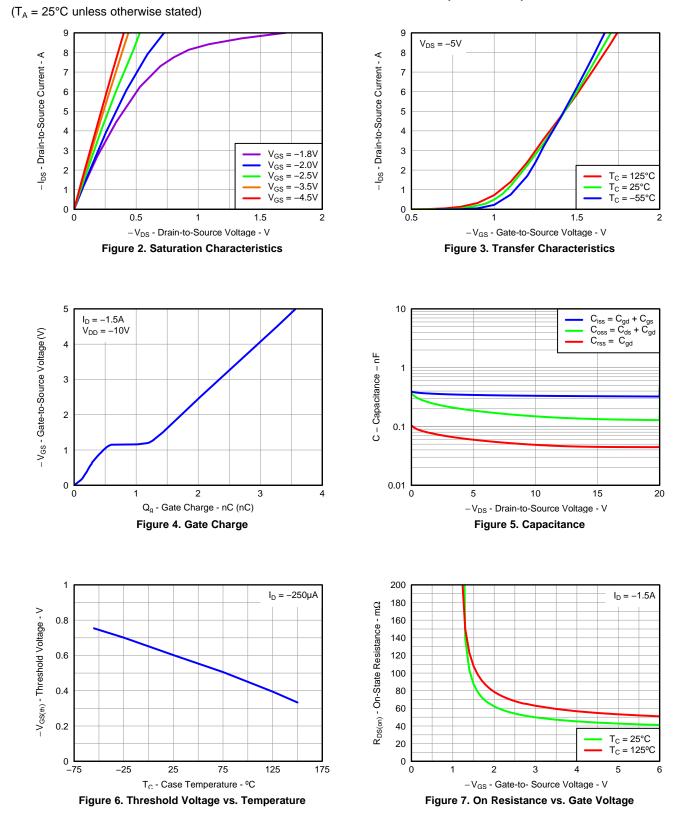


Figure 1. Transient Thermal Impedance

SLPS292-JANUARY 2011

TYPICAL MOSFET CHARACTERISTICS (continued)



4

ISTRUMENTS

FEXAS

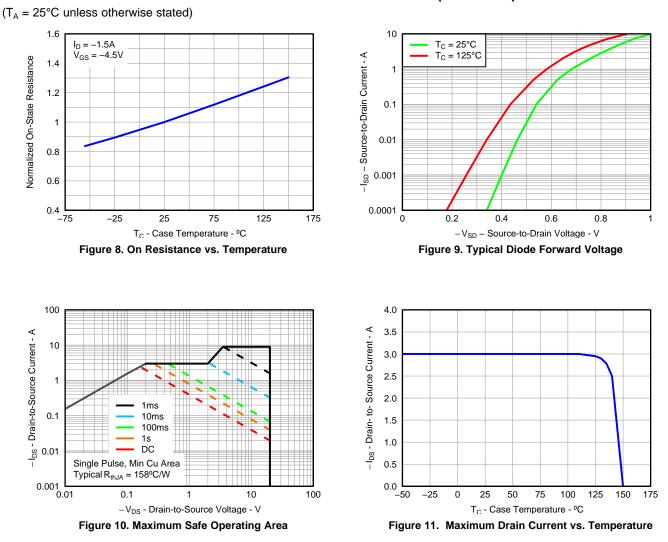
www.ti.com



SLPS292-JANUARY 2011

www.ti.com

TYPICAL MOSFET CHARACTERISTICS (continued)

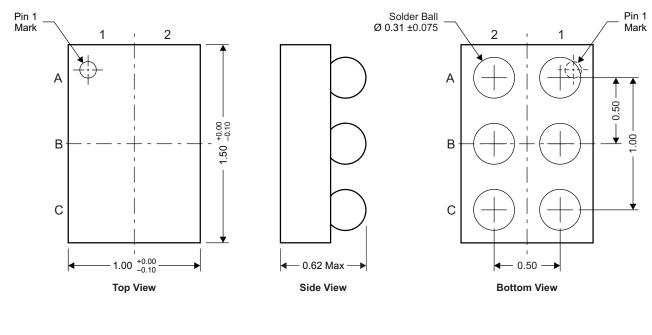


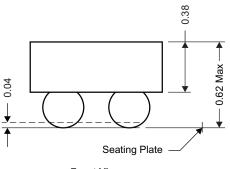
www.ti.com

SLPS292-JANUARY 2011

MECHANICAL DATA







Front View

M0157-01

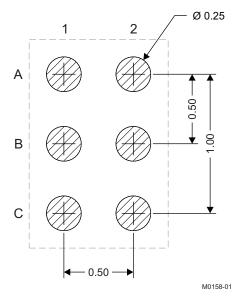
NOTE: All dimensions are in mm (unless otherwise specified)

Pinout						
POSITION	DESIGNATION					
C1, C2	Drain					
A1	Gate					
A2, B1, B2	Source					

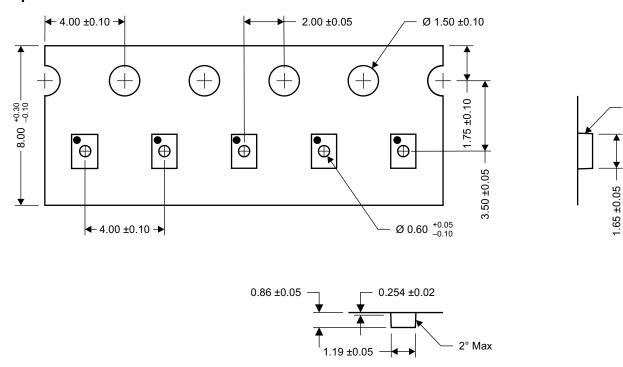


SLPS292-JANUARY 2011

Land Pattern Recommendation



NOTE: All dimensions are in mm (unless otherwise specified)



Tape and Reel Information

M0159-01

2° Max

NOTE: All dimensions are in mm (unless otherwise specified)



11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
CSD25303W1015	ACTIVE	DSBGA	YZC	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-55 to 150		Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

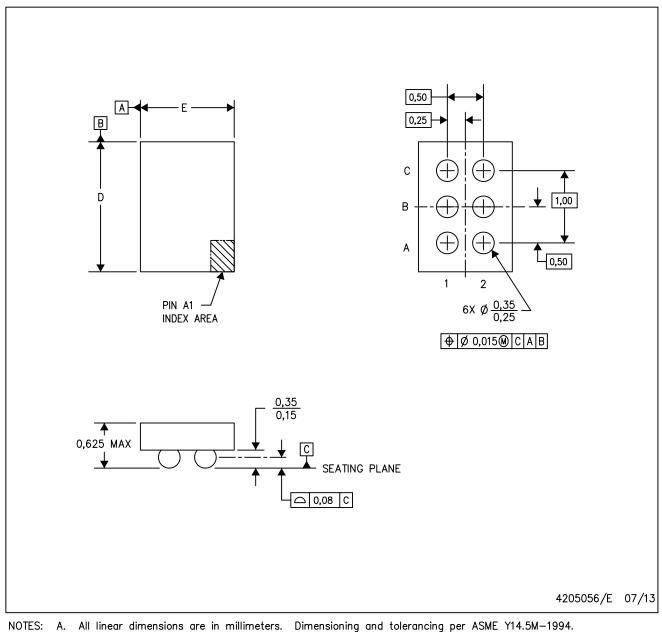
(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconne	ectivity	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2013, Texas Instruments Incorporated